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Application Number	10/670,928
Filing Date	September 25, 2003
First Named Inventor	Chun-Li Liu et al.
Group Art Unit	2812
Examiner Name	Unassigned
Attorney Docket Number	SC12851ZP

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number -Kind Code ² (if known)			
Dhe	B1	5,534,713	07/09/1996	Ismail <i>et al.</i>	
	B2	5,846,857	12/08/1998	Ju	
	B3	5,943,565	08/24/1999	Ju	
	B4	5,998,807	12/07/1999	Lustig <i>et al.</i>	
	B5	6,059,895	05/09/2000	Chu <i>et al.</i>	
	B6	6,124,627	09/26/2000	Rodder <i>et al.</i>	
	B7	2001/0048119 A1	12/06/2001	Mizuno <i>et al.</i>	
	B8	6,339,232 B1	01/15/2002	Takagi	
	B9	6,621,131 B2	09/16/2003	Murthy <i>et al.</i>	
Dhe	B10	6,638,802 B1	10/28/2003	Hwang <i>et al.</i>	

FOREIGN PATENT DOCUMENTS

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	B12	Jung <i>et al.</i> , "Implementation of Both High-Hole and Electron Mobility in Strained Si/Strained Si _{1-y} Ge on Relaxed Si _{1-x} Ge _(x<y) Virtual Substrate," <i>IEEE Electron Device Letters</i> , Vol. 24, No. 7, July 2003, pp. 460-462.	
	B13	Tezuka <i>et al.</i> , "Ultrathin Body SiGe-on-Insulator pMOSFETs with High-Mobility SiGe Surface Channels," <i>IEEE Transactions on Electron Devices</i> , Vol. 50, No. 5, May 2003, pp. 1328-1333.	

Examiner Signature	Dle	Date Considered	4/2005
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